

2SD788

Silicon NPN Epitaxial

REJ03G0771-0200
 (Previous ADE-208-1139)
 Rev.2.00
 Aug.10.2005

Application

- Low frequency power amplifier
- Complementary pair with 2SB738 and 2SB739

Outline

RENESAS Package code: PRSS0003DC-A
 (Package name: TO-92 Mod)



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	2	A
Collector power dissipation	P_C	0.9	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-50 to +150	°C

Electrical Characteristics

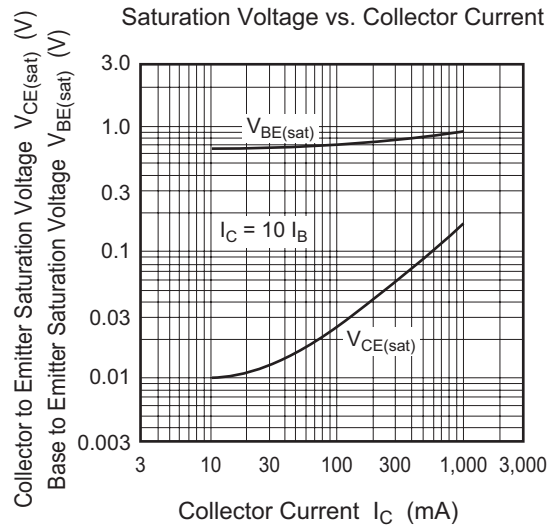
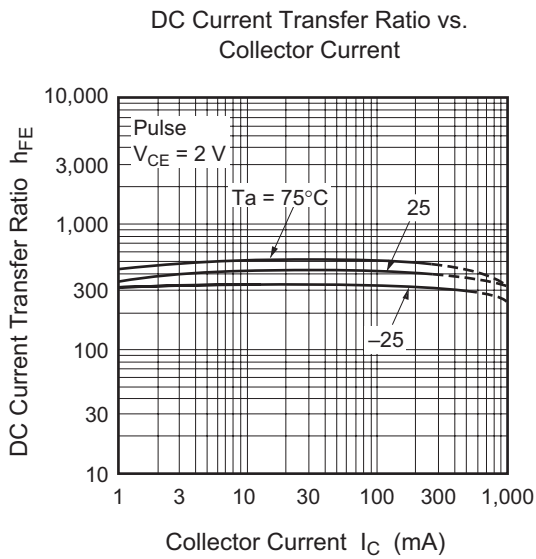
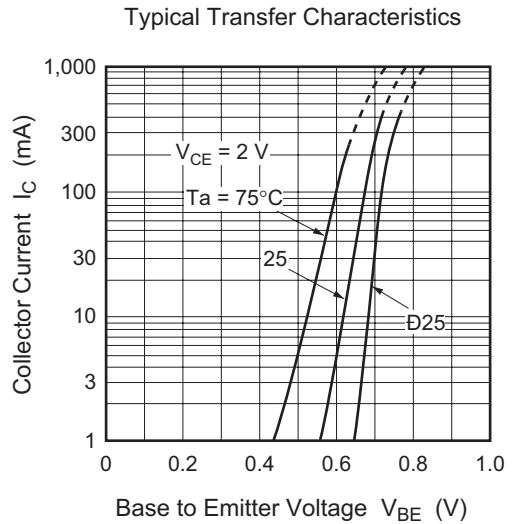
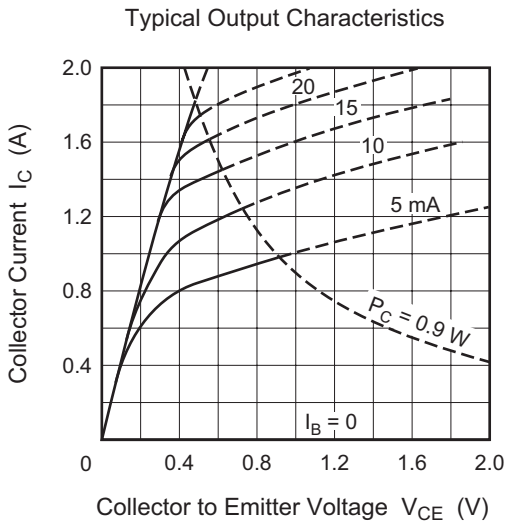
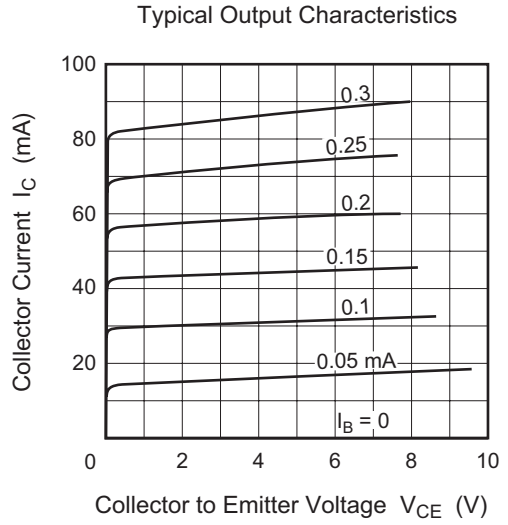
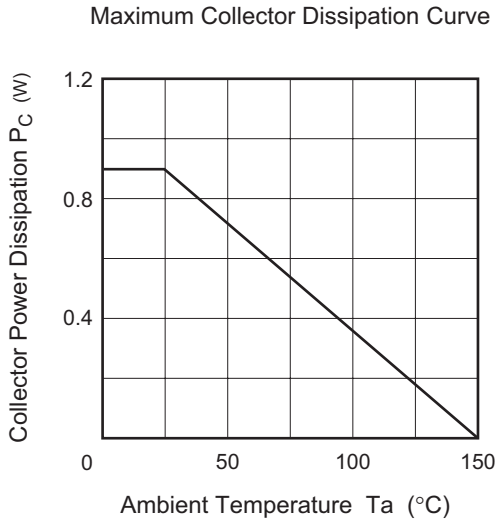
(Ta = 25°C)

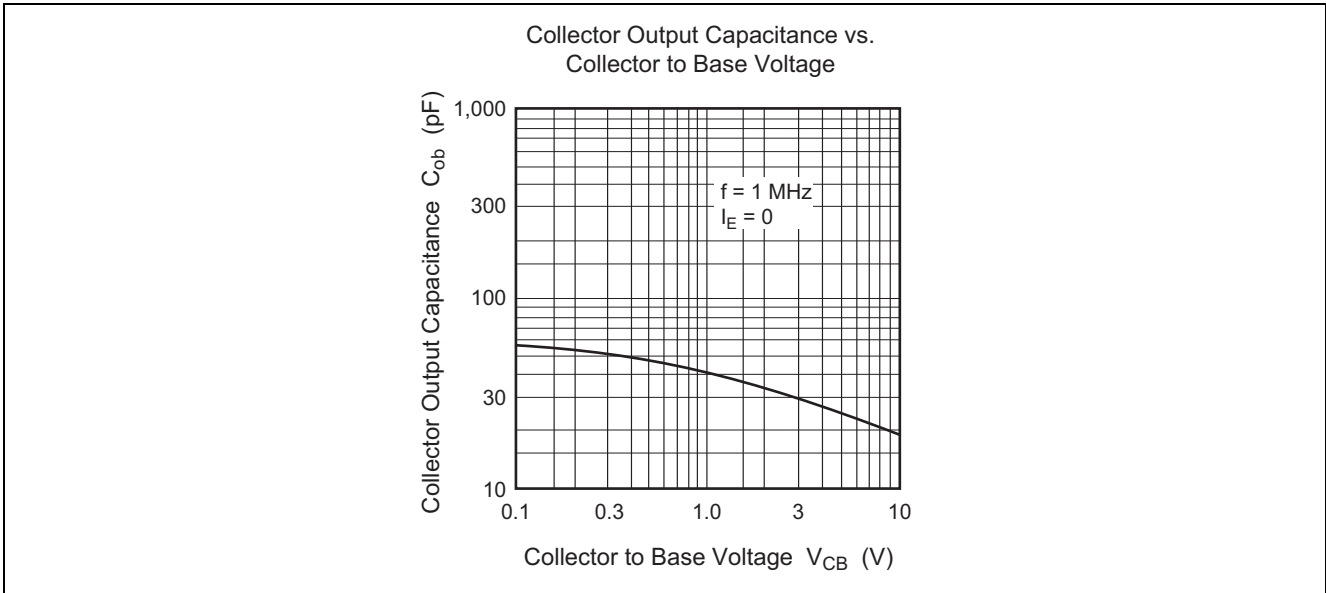
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	2	μA	$V_{CB} = 16 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.2	μA	$V_{EB} = 6 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	160	—	500		$V_{CE} = 2 \text{ V}, I_C = 0.1 \text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 1 \text{ A}, I_B = 0.1 \text{ A}$
Gain bandwidth product	f_T	—	100	—	MHz	$V_{CE} = 2 \text{ V}, I_C = 10 \text{ mA}$
Collector output capacitance	C_{ob}	—	20	—	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SD788 is grouped by h_{FE} as follows.

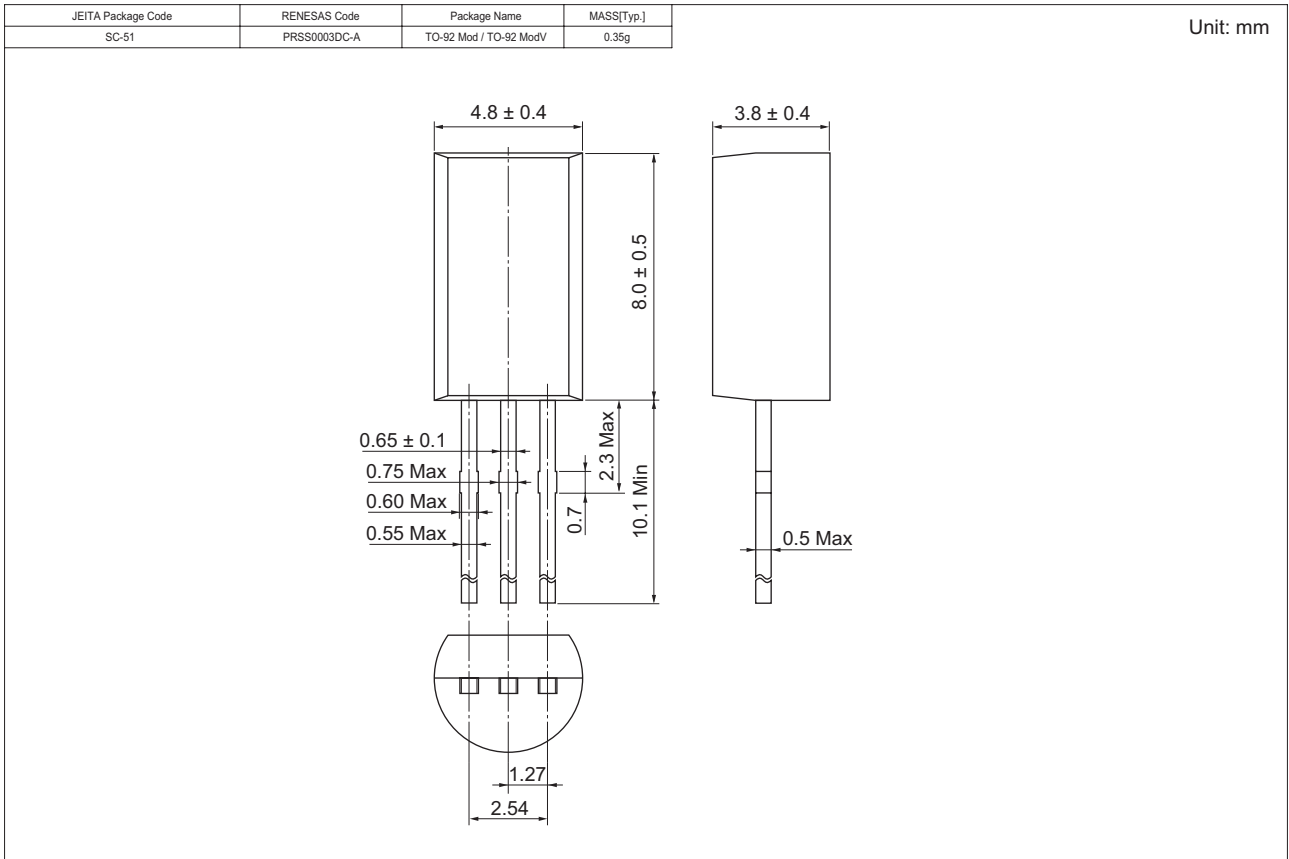
C	D
160 to 320	250 to 500

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SD788CTZ-E 2SD788DTZ-E	2500	Hold Box, Radial Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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